

Silicon PNP Power Transistors**2SA1104****DESCRIPTION**

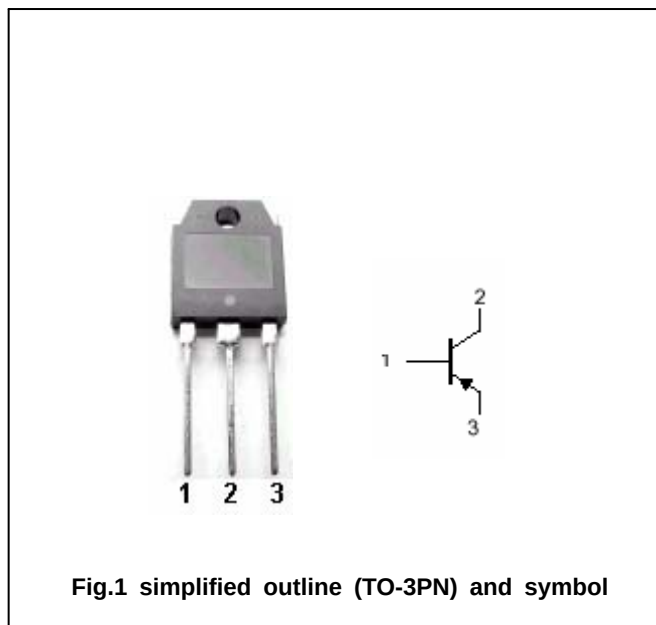
- With TO-3PN package
- High frequency
- High power dissipation

APPLICATIONS

- For use in audio and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

**Absolute maximum ratings(Ta=°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-120	V
V _{CEO}	Collector-emitter voltage	Open base	-120	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-8	A
P _C	Collector power dissipation	T _C =25°C	80	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

Silicon PNP Power Transistors**2SA1104****CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-25mA ; I _B =0	-120			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3A; I _B =-0.3A			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-3A; I _B =-0.3A			-1.8	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V; I _E =0			-100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-100	μ A
h _{FE}	DC current gain	I _C =-3A ; V _{CE} =4V	50		180	
f _T	Transition frequency	I _E =1A ; V _{CE} =-12V		20		MHz

2SA1104

The technical drawing shows two views of a mechanical component. The left view is a front elevation with vertical dimensions on the left (0.00 to 42.60) and horizontal dimensions at the top (8.00 to 15.60). It features a central rectangular cutout with rounded corners (R0.50), three small circular holes, and a larger circular hole. The right view is a side elevation showing the profile of the component with dimensions such as 4.80, 7.00, 17.00, and 40.10. It includes a circular feature with a radius of R5.50 and several vertical slots. Tolerances are specified for certain dimensions, such as 2.00 ± 0.005 , 0.60 ± 0.005 , $3.40^{+0.05}_0$, and 10.90 ± 0.01 .